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SOT-89 NPN Silicon NPN transistor in a SOT-89 Plastic Package.

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, BC869

Low voltage, high current, Complementary to BC869.

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General purpose switching and amplification, such as audio output stages.

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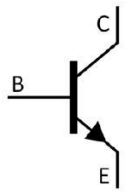

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PIN1 Base PIN 2 Collector PIN 3 Emitter

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Marking	HCAC⁑

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Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	32	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current-Continuous	I_C	1.0	A
Peak Collector Current	I_{CM}	2.0	A
Peak Base Current	I_{BM}	200	mA
Collector Power Dissipation	P_C	1.35	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

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Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=25V I_E=0			0.1	μA
Emitter Base Cut-Off Current	I_{EBO}	V_{EB}=5.0V I_C=0			0.1	μA
DC Current Gain	$h_{FE(1)}$	V_{CE}=1.0V I_C=500mA	85		375	
	$h_{FE(2)}$	V_{CE}=10V I_C=5.0mA	50			
	$h_{FE(3)}$	V_{CE}=1.0V I_C=1.0A	60			
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=1.0A I_B=100mA			500	mV
Base to Emitter Voltage	$V_{BE(1)}$	V_{CE}=10V I_C=5.0mA		620		mV
	$V_{BE(2)}$	V_{CE}=1.0V I_C=1.0A			1.0	V
Transition Frequency	f_T	V_{CE}=5.0V I_C=10mA f=100MHz	40			MHz

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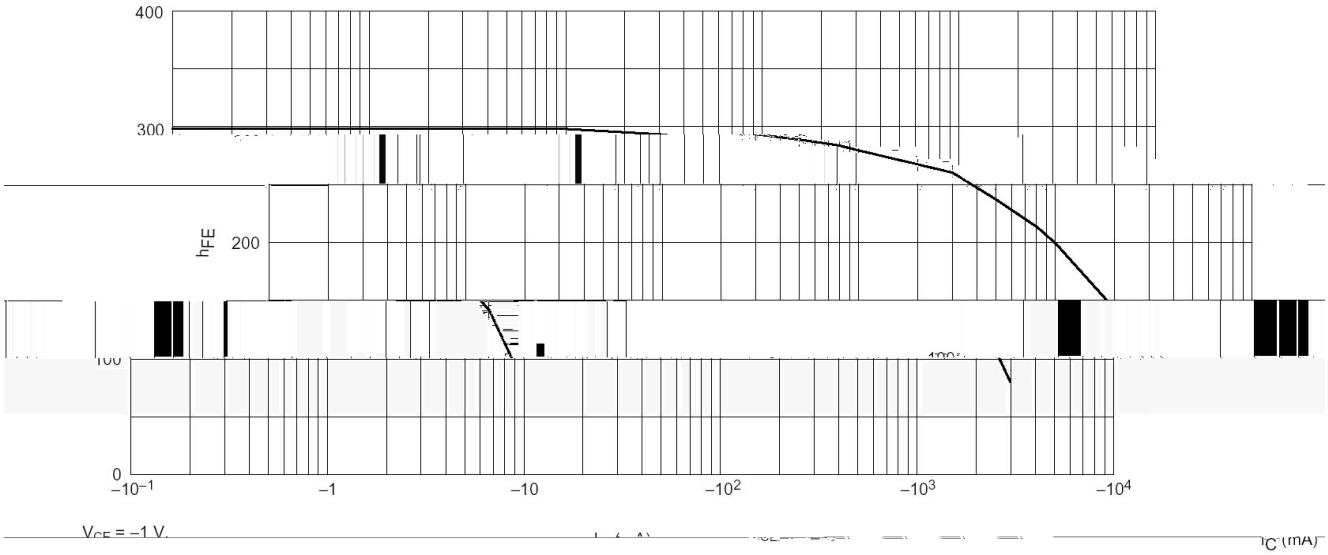

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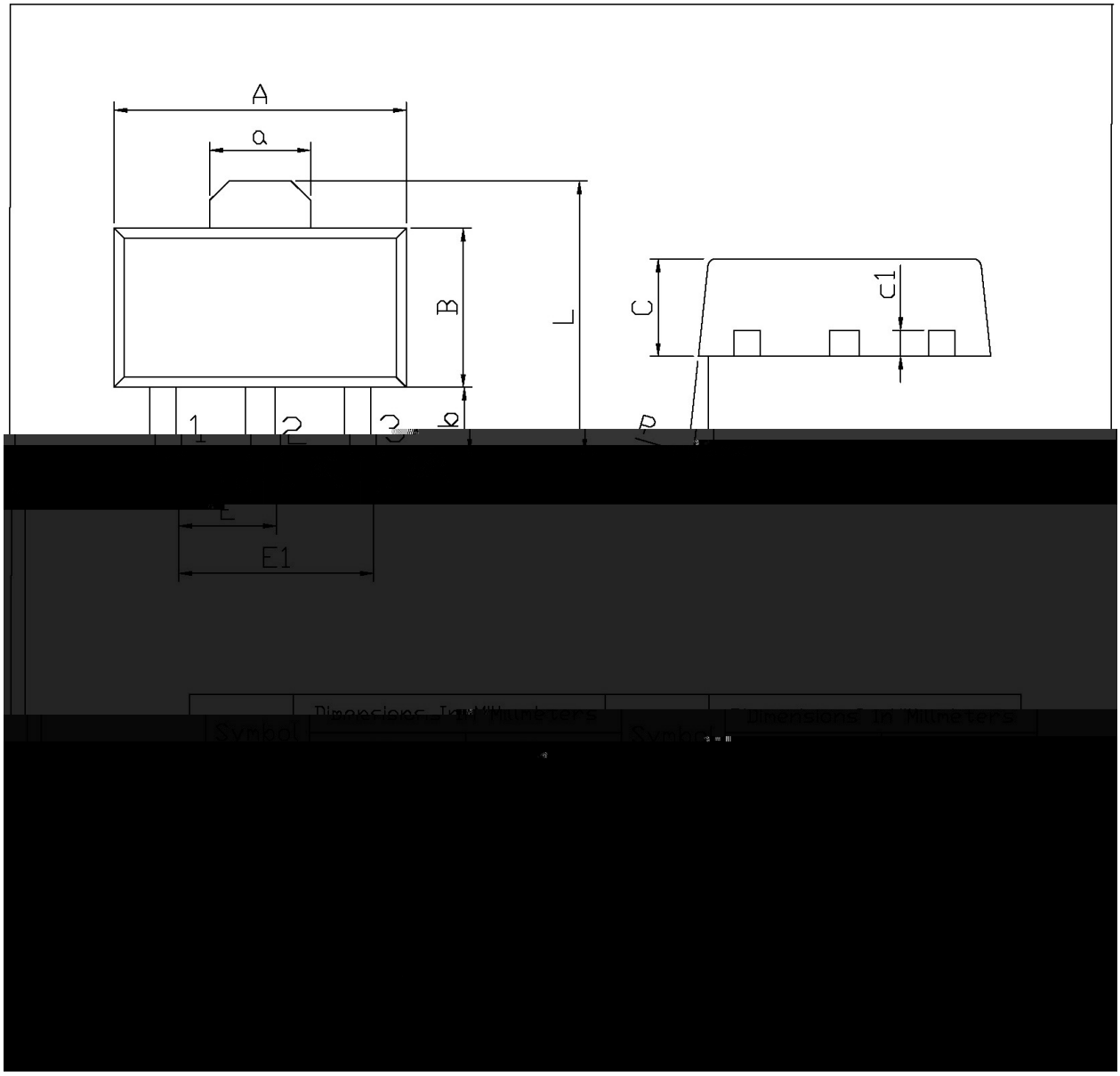
SOT-89

单位：mm



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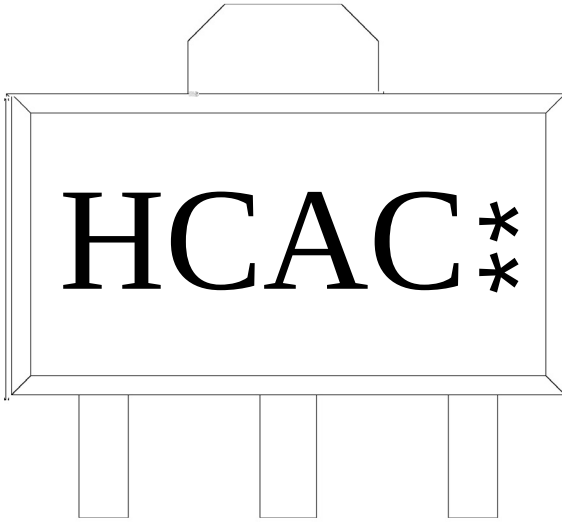

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CAC

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Note:

H: Company Code.

CAC: Product Type.

**: Lot No. Code, code change with Lot No.

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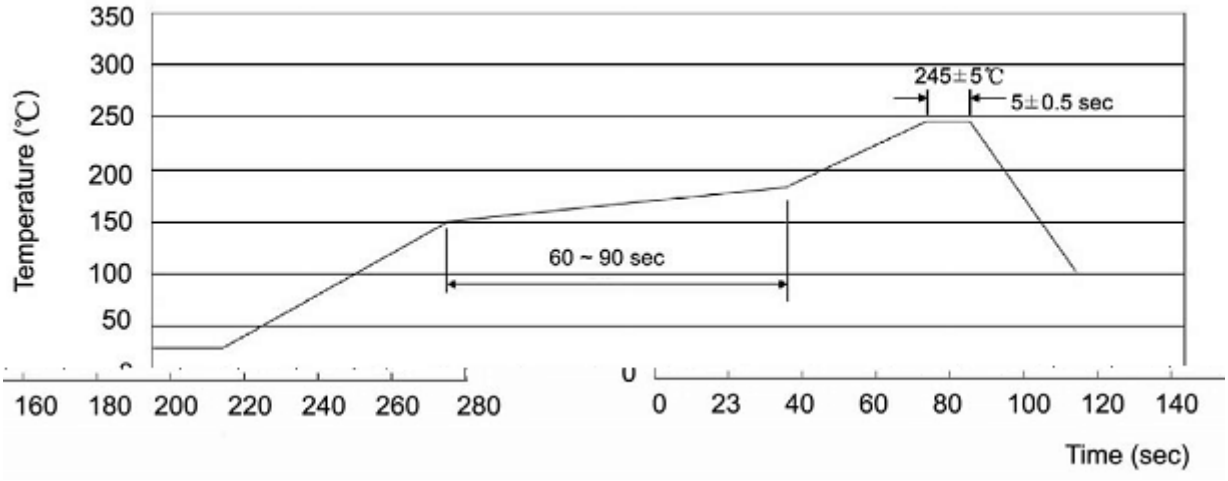

	Note:
1 25 150 60 90sec;	1.Preheating:25~150 , Time:60~90sec.
2 245±5 5±0.5sec;	2.Peak Temp.:245±5 , Duration:5±0.5sec.
3 2 10 /sec.	3. Cooling Speed: 2~10 /sec.

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260±5 10±1 sec. Temp.:260±5℃ Time:10±1 sec

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Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm^3)		
	只 卷盘	卷盘 盒	只 盒	盒 箱	只 箱		盒	箱

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